

ABSTRACT OF THE DISCLOSURE

The purpose of the present invention is to provide a small-sized switch attaining high isolation of not less than 80 dB, maintaining low insertion loss also in high frequencies not less than 60 GHz. A semiconductor switch according to the present invention utilizes FETs a gate electrode, a source electrode, and a drain electrode of each of which are formed on a semiconductor. The source electrode and the drain electrode are connected with the earth as well as are disposed in parallel to each other, and the gate electrode is formed between the source electrode and the drain electrode, and both the ends of the gate electrode are connected to the first input-output terminal 1 and the second input-output terminal.